



# PSMN5R6-100YSF

NextPower 100 V, 6 mΩ N-channel MOSFET in LFPACK56 package

19 February 2018

Preliminary data sheet

## 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

## 2. Features and benefits

- Low  $Q_{rr}$  for higher efficiency and lower spiking
- Qualified to 175 °C
- Low  $Q_G \times R_{DSon}$  FOM for high efficiency switching applications
- Strong avalanche energy rating ( $E_{as}$ )
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LFPACK56 package
- Wave-solderable LFPACK56 package

## 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- BLDC motor control
- USB-PD and mobile fast-charge adapters
- LED lighting
- Full-bridge and half-bridge applications
- Flyback and resonant topologies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	294	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	4.5	5.6	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 100\text{ °C}$ ; <a href="#">Fig. 11</a>	-	7.3	8.7	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 50\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	13.5	-	nC
$Q_{G(tot)}$	total gate charge		-	65.1	-	nC

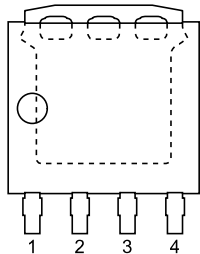
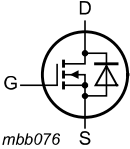
NextPower 100 V, 6 mΩ N-channel MOSFET in LFPAK56 package

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Avalanche ruggedness</b>							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 41.8\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{J(\text{init})} = 25\text{ }^\circ\text{C}$ ; Fig. 4; Unclamped	[1]	-	-	440	mJ
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; Fig. 16	-	67.3	-	nC	

[1] Protected by 100% test

### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFPAK56E; Power-SO8 (SOT1023)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

### 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R6-100YSF	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch; 4.58 mm x 5.13 mm x 1.03 mm body	SOT1023

### 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN5R6-100YSF	5F6S10

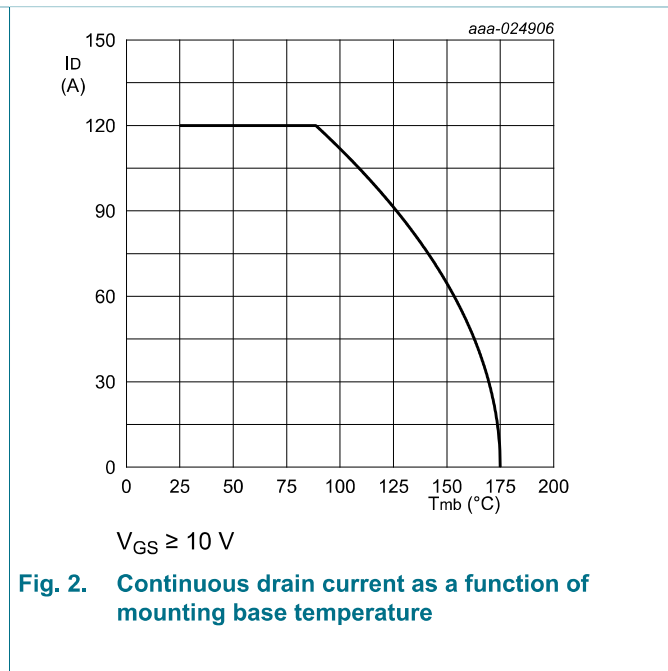
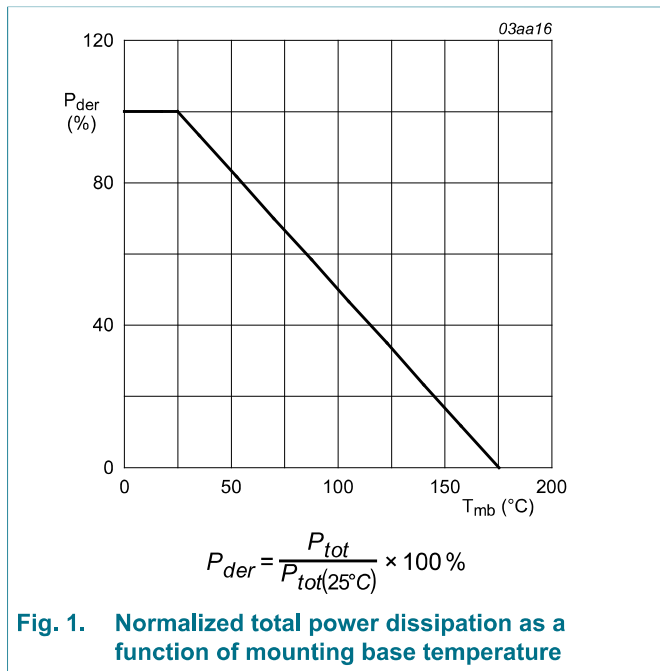
### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>	-	294	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>	-	120	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <a href="#">Fig. 2</a>	-	112	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 3</a>	-	480	A
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	480	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 41.8 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; <a href="#">Fig. 4</a> ; Unclamped	[1]	-	440 mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> ≤ 100 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω	[1]	-	41.8 A

[1] Protected by 100% test



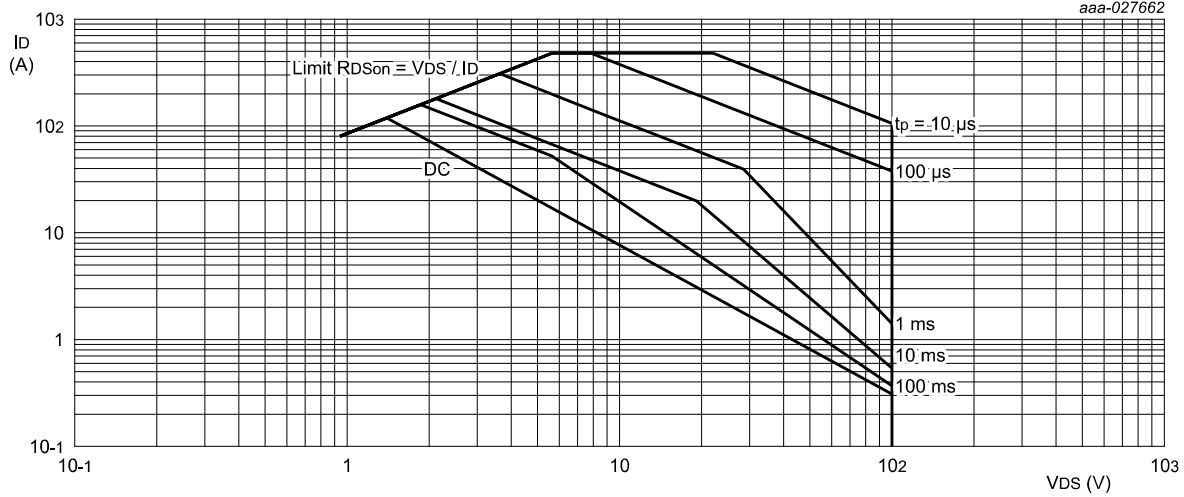
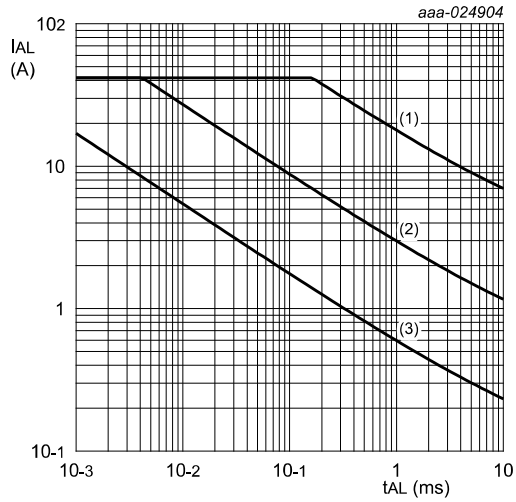


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j(init)} = 25 \text{ }^\circ\text{C}$ ; (2)  $T_{j(init)} = 150 \text{ }^\circ\text{C}$ ; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.45	0.51	K/W

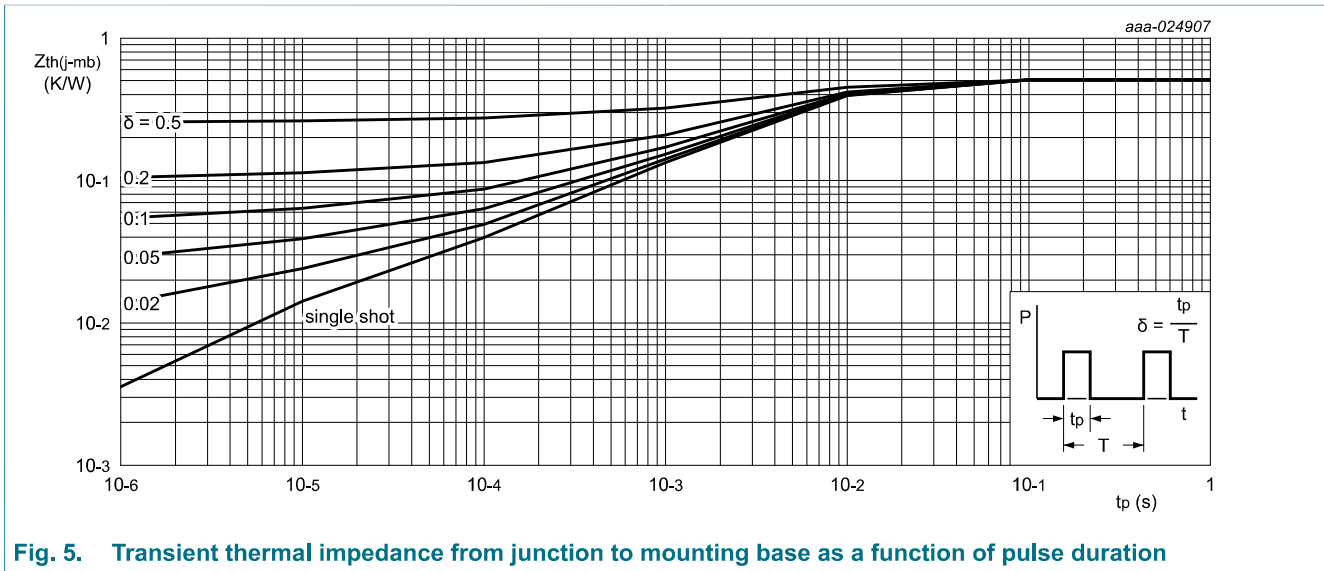


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$	-	3.6	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$	-	1.8	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 9}$	2	3.1	4	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 175 \text{ }^\circ C$	-	-8.8	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.03	5	$\mu A$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	-	100	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	5	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	5	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C; \text{ Fig. 10}$	-	4.5	5.6	mΩ
		$V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C; \text{ Fig. 10}$	-	5.1	7.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ C; \text{ Fig. 11}$	-	7.3	8.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C; \text{ Fig. 11}$	-	10.3	12.3	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	0.9	-	Ω

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	65.1	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	32.2	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	20.4	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	12.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	7.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	13.5	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>	-	4616	-	pF
C <sub>oss</sub>	output capacitance		-	805	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	12	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	17.4	-	ns
t <sub>r</sub>	rise time		-	16.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	35.1	-	ns
t <sub>f</sub>	fall time		-	19.7	-	ns
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; <a href="#">Fig. 16</a>	-	51.4	-	ns
Q <sub>r</sub>	recovered charge		-	67.3	-	nC

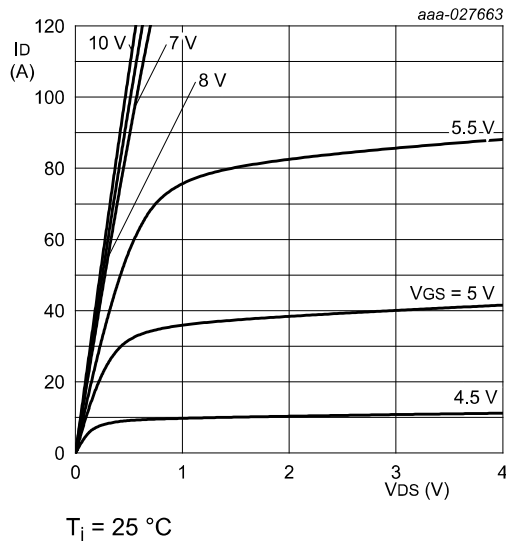


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

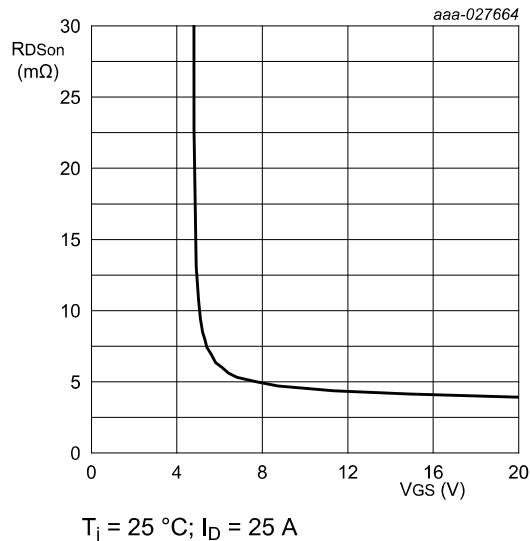


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

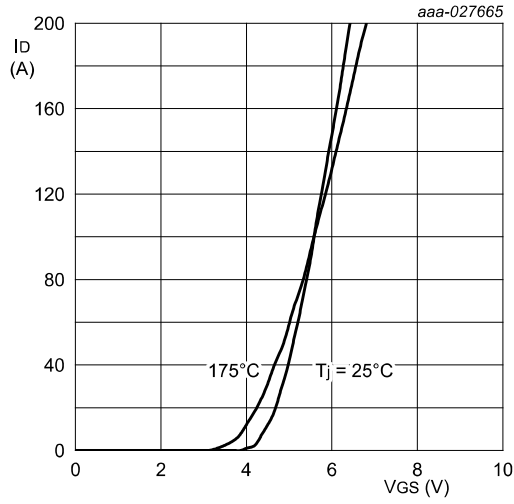


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

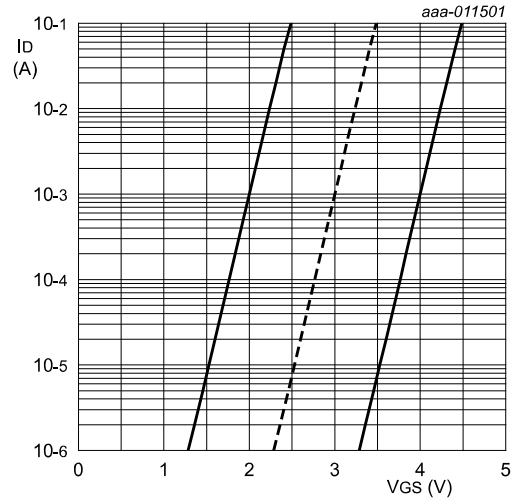


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

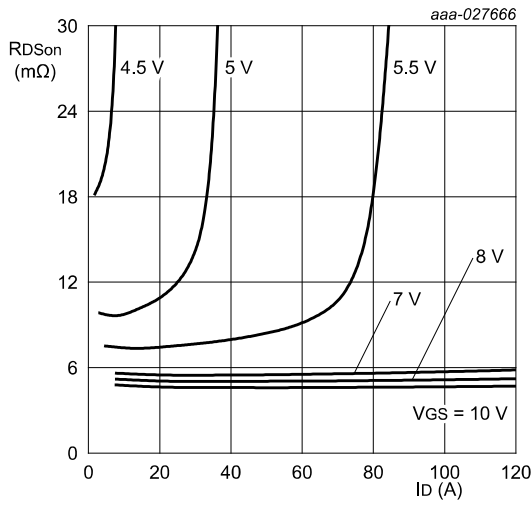
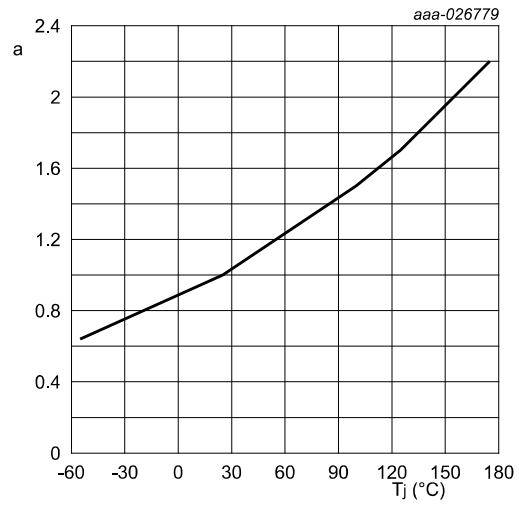
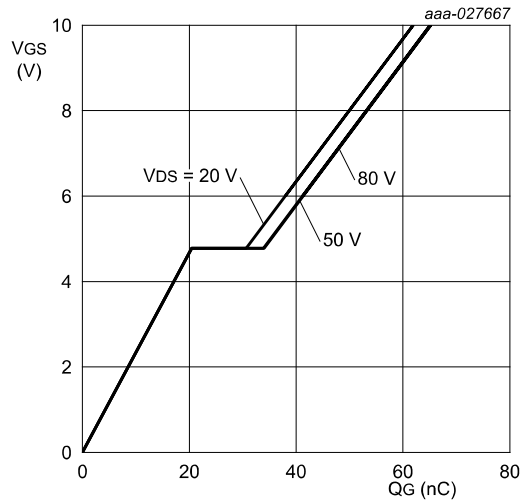


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



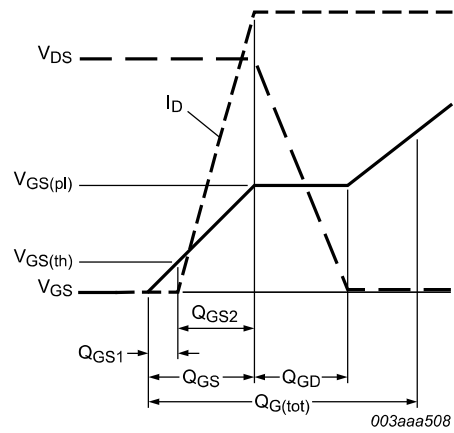
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

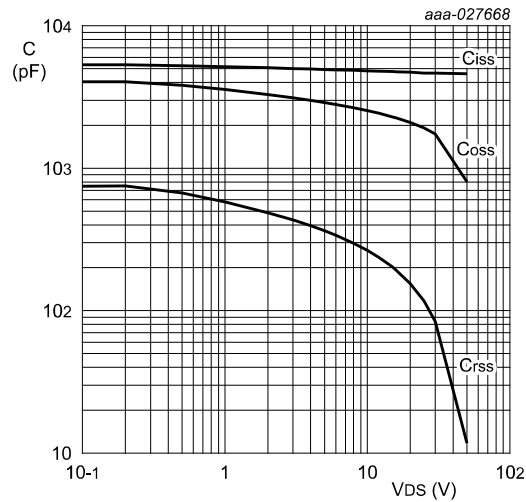


$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

**Fig. 12. Gate-source voltage as a function of gate charge; typical values**

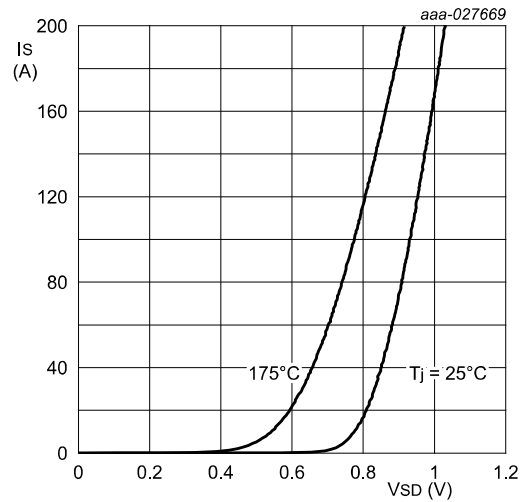


**Fig. 13. Gate charge waveform definitions**



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0\text{ V}$

**Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



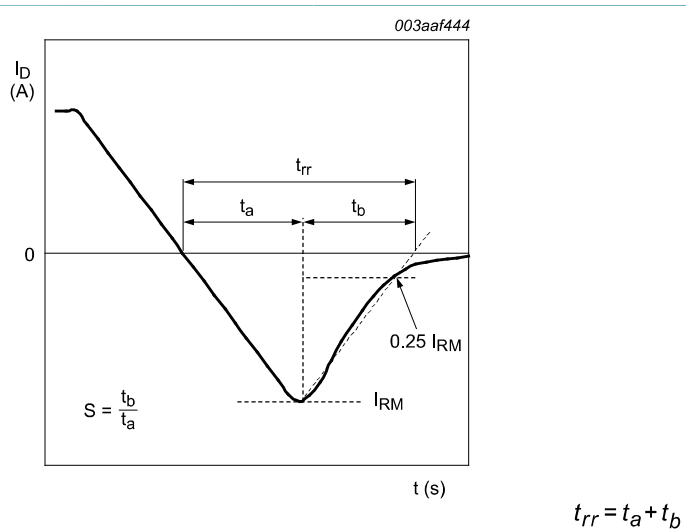


Fig. 16. Reverse recovery waveform definitions

### 11. Package outline

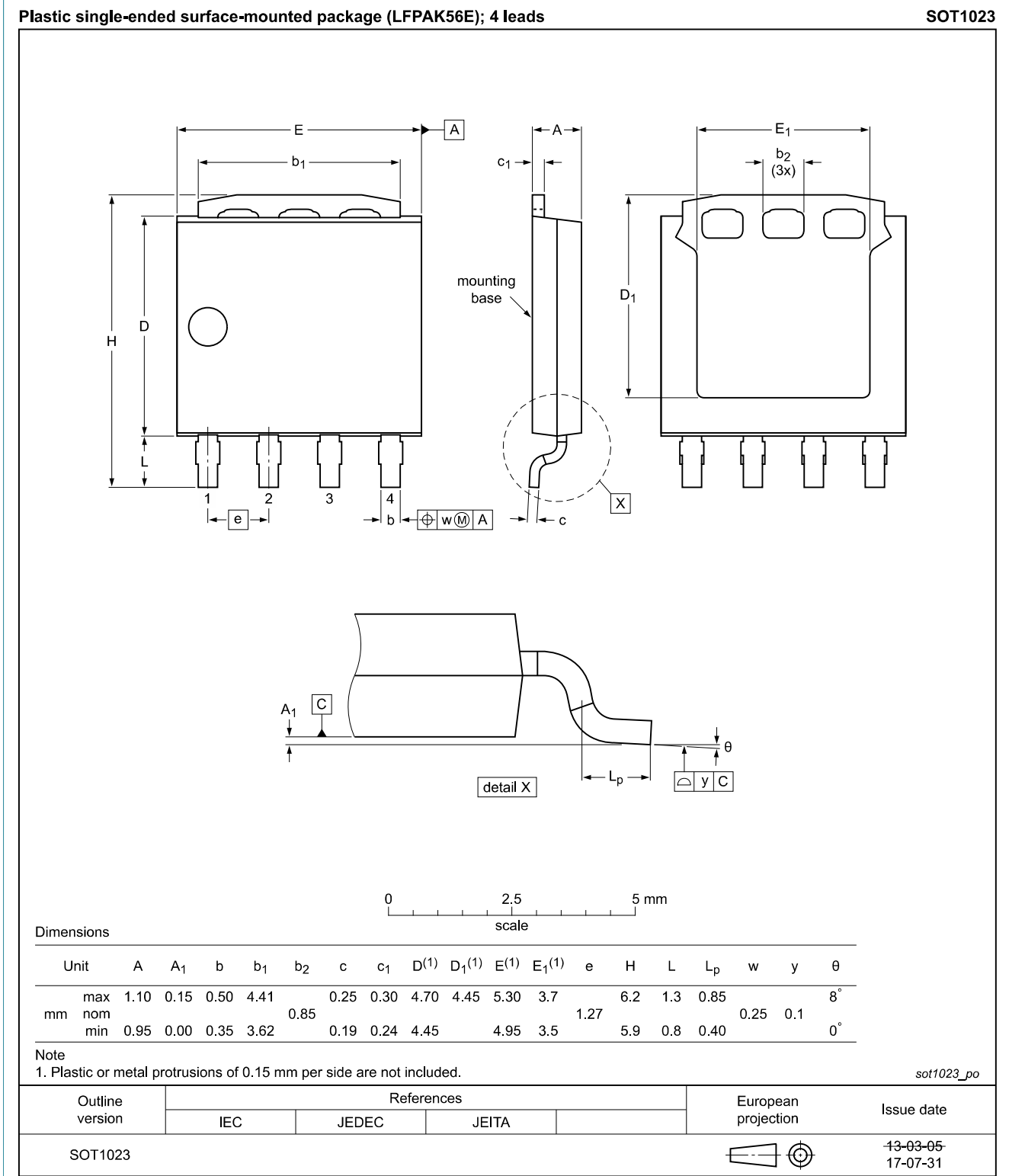


Fig. 17. Package outline LFPAK56E; Power-SO8 (SOT1023)

## 12. Soldering

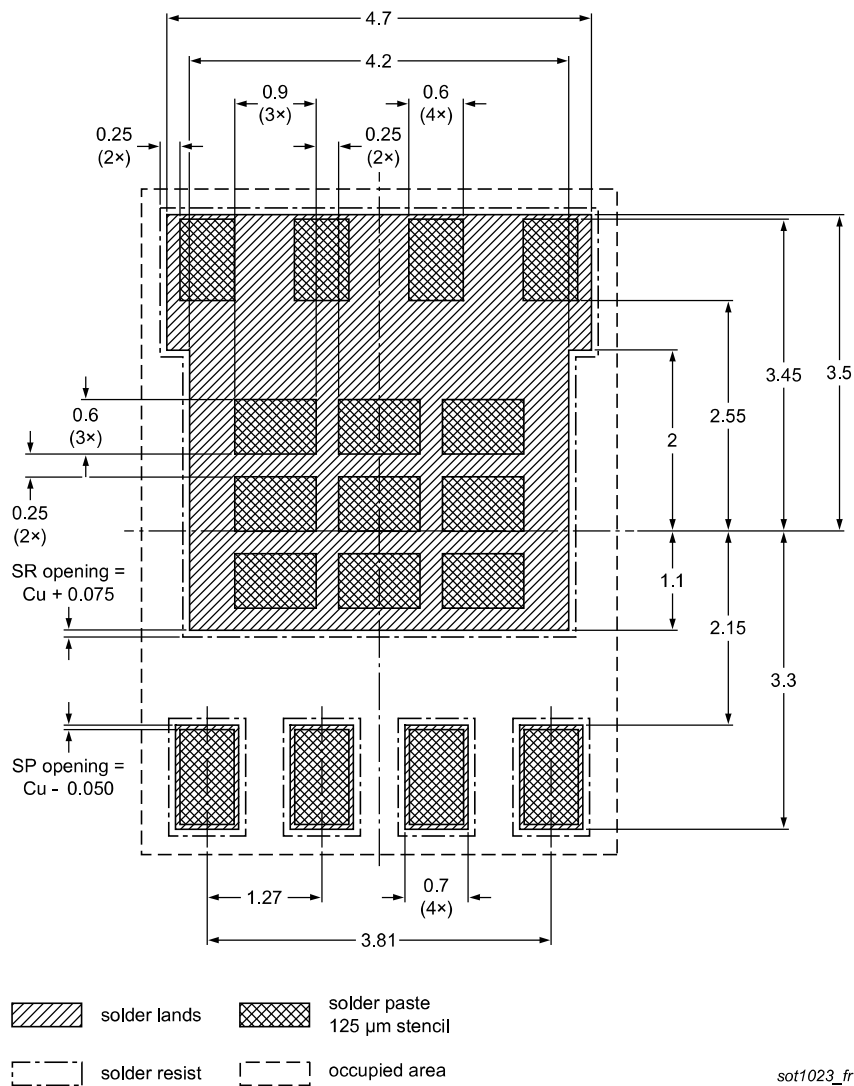


Fig. 18. Reflow soldering footprint for LFPAK56E; Power-SO8 (SOT1023)

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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